

# SILICON POWER MOS FET NE5531079A

# 7.5 V OPERATION SILICON RF POWER LDMOS FET FOR UHF-BAND 10 W TRANSMISSION AMPLIFIERS

# DESCRIPTION

The NE5531079A is an N-channel silicon power laterally diffused MOS FET specially designed as the transmission power amplifier for 7.5 V radio systems. Dies are manufactured using our NEWMOS-M1 technology and housed in a surface mount package. This device can deliver 40.0 dBm output power with 68% power added efficiency at 460 MHz under the 7.5 V supply voltage.

: Pout = 40.0 dBm TYP. (VDs = 7.5 V, IDset = 200 mA, f = 460 MHz, Pin = 25 dBm)

: GL = 20.5 dB TYP. (VDS = 7.5 V, IDset = 200 mA, f = 460 MHz, Pin = 10 dBm)

# FEATURES

- High output power
- High power added efficiency :  $\eta_{add} = 68\%$  TYP. (VDs = 7.5 V, IDset = 200 mA, f = 460 MHz, Pin = 25 dBm)
- High linear gain
- Surface mount package
- Single supply

# **APPLICATIONS**

- 460 MHz band radio systems
- 900 MHz band radio systems

# **ORDERING INFORMATION**

Part Number	Order Number	Package	Marking	Supplying Form
NE5531079A	NE5531079A-A	79A (Pb-Free)	W5	<ul><li>12 mm wide embossed taping</li><li>Gate pin face the perforation side of the tape</li></ul>
NE5531079A-T1	NE5531079A-T1-A			<ul> <li>12 mm wide embossed taping</li> <li>Gate pin face the perforation side of the tape</li> <li>Qty 1 kpcs/reel</li> </ul>
NE5531079A-T1A	NE5531079A-T1A-A			<ul> <li>12 mm wide embossed taping</li> <li>Gate pin face the perforation side of the tape</li> <li>Qty 5 kpcs/reel</li> </ul>

**Remark** To order evaluation samples, please contact your nearby sales office. Part number for sample order: NE5531079A

:  $5.7 \times 5.7 \times 1.1$  mm MAX.

: VDS = 7.5 V MAX.

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all products and/or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.

**ABSOLUTE MAXIMUM RATINGS (T**<sub>A</sub> = +25°C) Operation in excess of any one of these parameters may result in permanent damage.

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	VDS Note 1	30	V
Gate to Source Voltage	Vgs	6.0	V
Drain Current	los	3.0	А
Drain Current (Pulse Test)	DS Note 2	6.0	А
Total Power Dissipation	Ptot	35	W
Channel Temperature	Tch	125	°C
Storage Temperature	Tstg	-55 to +125	°C

Note 1. VDS will be used under 12 V on RF operation.

**2.** Duty Cycle  $\leq$  50%, Ton  $\leq$  1 s

### **RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	VDS		-	6.0	7.5	V
Gate to Source Voltage	V <sub>GS</sub>		1.15	1.55	2.05	V
Drain Current	los		_	2.0	_	А
Input Power	Pin	f = 460 MHz, V <sub>DS</sub> = 6.0 V	-	25	30	dBm

# **ELECTRICAL CHARACTERISTICS**

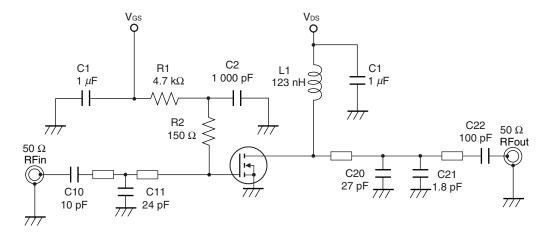
# (TA = +25°C, unless otherwise specified, using our standard test fixture)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leakage Current	lgss	V <sub>GS</sub> = 6.0 V	-	-	100	nA
Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	loss	V <sub>DS</sub> = 25 V	_	-	10	nA
Gate Threshold Voltage	Vth	Vbs = 7.5 V, lbs = 1.0 mA	0.8	1.15	1.55	V
Thermal Resistance	Rth	Channel to Case	-	2.9	-	°C/W
Transconductance	Яm	V <sub>DS</sub> = 7.5 V, I <sub>DS</sub> = 700±100 mA	2.5	3.2	4.0	S
Drain to Source Breakdown Voltage	BVDSS	IDSS = 10 $\mu$ A	25	35	-	V
Output Power	Pout	f = 460 MHz, V <sub>DS</sub> = 7.5 V,	39.0	40.0	-	dBm
Drain Current	los	Pin = 25 dBm,	-	2.0	-	А
Power Added Efficiency	$\eta_{ m add}$	I <sub>Dset</sub> = 200 mA (RF OFF)	_	68	-	%
Linear Gain	GL <sup>Note</sup>		_	20.5	_	dB

#### Note Pin = 10 dBm

DC performance is 100% testing. RF performance is testing several samples per wafer. Wafer rejection criteria for standard devices is 1 reject for several samples.

# TEST CIRCUIT (f = 460 MHz)

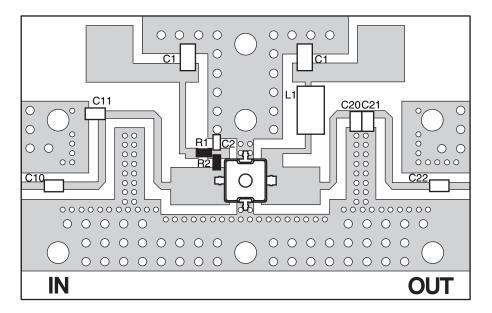


The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

Symbol	Value	Туре	Maker
C1	1 <i>µ</i> F	GRM31CR72A105KA01B	Murata
C2	1 000 pF	GRM1882C1H102JA01	Murata
C10	10 pF	GRM1882C1H100JA01	Murata
C11	24 pF	ATC100A240JW	American Technical Ceramics
C20	27 pF	ATC100A270JW	American Technical Ceramics
C21	1.8 pF	ATC100A1R8BW	American Technical Ceramics
C22	100 pF	ATC100A101JW	American Technical Ceramics
R1	4.7 kΩ	1/8W Chip Resistor	_
R2	150 Ω	1/8W Chip Resistor	_
L1	123 nH	$\phi$ 0.5 mm, $\phi$ D = 3 mm, 10 Turns	Ohesangyou
PCB	-	R4775, t = 0.4 mm, $\epsilon$ r = 4.5, size = 30 × 48 mm	-

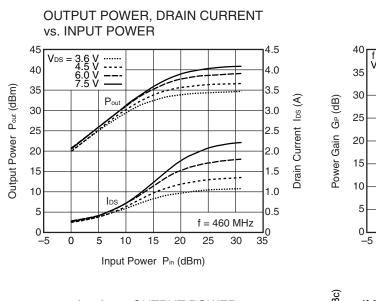
#### COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

# ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



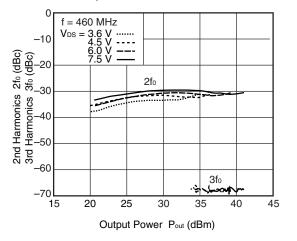
# USING THE NEC EVALUATION BOARD

Symbol	Value	
C1	1 <i>µ</i> F	
C2	1 000 pF	
C10	10 pF	
C11	24 pF	
C20	27 pF	
C21	1.8 pF	
C22	100 pF	
R1 4.7 kΩ		
R2	150 Ω	
L1 123 nH		



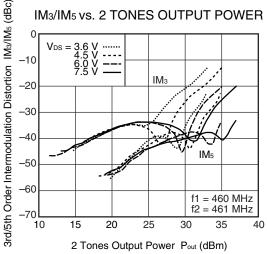
#### TYPICAL CHARACTERISTICS (TA = +25°C, IDset = 200 mA, unless otherwise specified)





Remark The graphs indicate nominal characteristics.

POWER GAIN, POWER ADDED EFFICIENCY vs. INPUT POWER 80 f = 460 MHz V<sub>DS</sub> = 3.6 V ..... 4.5 V ----6.0 V ----7.5 V ----70  $\eta_{add}$  (%) 60  $\eta_{add}$ Power Added Efficiency 50 40 GF 30 20 10 0 0 10 15 20 25 30 35 5 Input Power Pin (dBm)



# S-PARAMETERS

S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

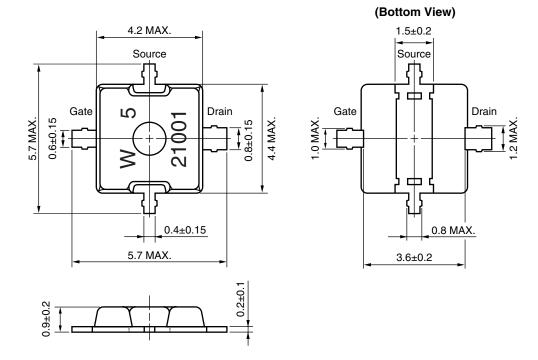
Click here to download S-parameters.

 $[\text{RF} \text{ and Microwave}] \rightarrow [\text{Device Parameters}]$ 

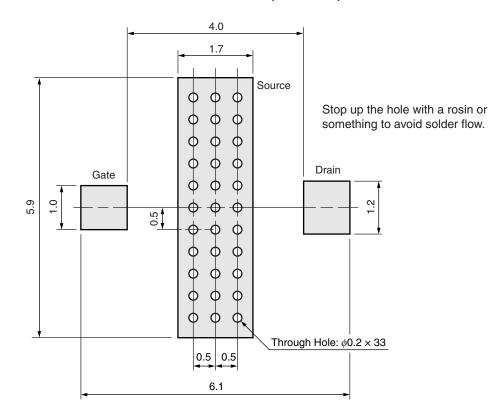
URL http://www.necel.com/microwave/en/

# PACKAGE DIMENSIONS

# 79A (UNIT: mm)



# 79A PACKAGE RECOMMENDED P.C.B. LAYOUT (UNIT: mm)



Data Sheet PU10752EJ01V0DS

# **RECOMMENDED SOLDERING CONDITIONS**

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) Soldering time (per pin of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350-P3

Caution Do not use different soldering methods together (except for partial heating).

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